

L Number	Hits	Search Text	DB	Time stamp
1	2	("5955772").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT	2003/08/06 14:34
-	1293	(AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As")		2001/10/09 15:41
-	1605	(AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/05/16 16:52
-	743	((AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As")) and 257/\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/05/16 11:17
-	672	(quantum adj well photo adj excit\$5 photoexcit\$5) and ((AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/05/16 11:23
-	331	((AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As")) and 257/\$) and ((quantum adj well photo adj excit\$5 photoexcit\$5) and ((AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As")))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/05/16 11:23
-	17	(quantum adj well) and (photo adj excit\$5 photoexcit\$5) and ((AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/05/16 11:24
-	0	((AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") with (barrier)) and (("Ga As" "GaAs" GaAs) with (substrate and storage)) and ((InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") with (quantum well))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/05/16 11:32
-	0	((AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") with (barrier buffer)) and (("Ga As" "GaAs" GaAs) with (substrate and storage)) and ((InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") with (quantum well))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/05/16 11:44
-	7	((AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") same (barrier buffer)) and (("Ga As" "GaAs" GaAs) same (substrate and storage)) and ((InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") same (quantum well))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/05/16 11:44
-	112	((AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") with (barrier buffer)) and (("Ga As" "GaAs" GaAs) with (substrate and (quantum storage))) and ((InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") with (quantum well))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/05/16 11:54

-	66	((((AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") with (barrier buffer)) and ((("Ga As" "GaAs" GaAs) with (substrate and (quantum storage))) and ((InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") with (quantum well))) and 257/\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/05/16 11:54
-	180	electromagnetic adj wave adj detector	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/05/16 11:55
-	0	((((AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") with (barrier buffer)) and ((("Ga As" "GaAs" GaAs) with (substrate and (quantum storage))) and ((InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") with (quantum well))) and (electromagnetic adj wave adj detector)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/05/16 11:55
-	29228	electromagnetic adj wave	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/05/16 11:56
-	180	(electromagnetic adj wave) and (electromagnetic adj wave adj detector)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/05/16 11:56
-	0	(electromagnetic adj wave) and (((AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") with (barrier buffer)) and ((("Ga As" "GaAs" GaAs) with (substrate and (quantum storage))) and ((InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") with (quantum well))) and 257/\$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/05/16 11:56
-	6	electromagnetic and (((AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") with (barrier buffer)) and ((("Ga As" "GaAs" GaAs) with (substrate and (quantum storage))) and ((InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") with (quantum well))) and 257/\$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/05/16 12:06
-	131	(first and third) adj (buffer barrier) adj (layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/05/16 12:42
-	0	((electromagnetic adj wave) and (electromagnetic adj wave adj detector)) and ((first and third) adj (buffer barrier) adj (layer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/05/16 12:43
-	1115	(first and third) adj (buffer barrier)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/05/16 12:43
-	0	((electromagnetic adj wave) and (electromagnetic adj wave adj detector)) and ((first and third) adj (buffer barrier))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/05/16 12:46

-	1589	(third) adj (buffer barrier)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/05/16 12:44
-	2	((electromagnetic adj wave) and (electromagnetic adj wave adj detector)) and ((third) adj (buffer barrier))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/05/16 16:10
-	1	("5506418").PN.	USPAT	2001/05/16 16:30
-	8	5506418.URPN.	USPAT	2001/05/16 16:12
-	8	electron adj storage adj layer	USPAT	2001/05/16 16:32
-	244	electron adj storage	USPAT	2001/05/16 16:32
-	479	electron near stor\$3	USPAT	2001/05/16 16:38
-	8	5506418.URPN.	USPAT	2001/05/16 16:36
-	4140	quantum adj well	USPAT	2001/05/16 16:38
-	15	(electron near stor\$3) and (quantum adj well)	USPAT	2001/05/16 16:39
-	17	5670790.URPN.	USPAT	2001/05/16 16:49
-	468	(AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and (sens\$5 detector)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/05/17 08:49
-	0	electromagnet\$5 and ((AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and (sens\$5 detector))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/05/17 08:47
-	74	electromagnet\$5 and ((AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and (sens\$5 detector))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/05/17 08:51
-	574	(AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and (sens\$5 detect\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/05/17 10:12
-	78	electromagnet\$5 and ((AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and (sens\$5 detect\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/05/17 08:51
-	215	(AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and (photosens\$5 photodetect\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/05/17 09:50
-	35	(AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and photo adj (sens\$5 detect\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/05/17 09:50

228	((AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and (photosens\$5 photodetect\$5)) ((AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and photo adj (sens\$5 detect\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/05/17 09:50
127	((((AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and (photosens\$5 photodetect\$5)) ((AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and photo adj (sens\$5 detect\$5))) and 257/\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/05/17 09:53
0	(((((AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and (photosens\$5 photodetect\$5)) ((AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and photo adj (sens\$5 detect\$5))) and 257/\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/05/17 09:53
24	(((((AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and (photosens\$5 photodetect\$5)) ((AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and photo adj (sens\$5 detect\$5))) and 257/\$) and graded near3 layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/05/17 10:07
672	(AlGaAs GaAlAs "GaAlAs" "Ga Al As" aluminum adj gallium adj arsinide "Al Ga As" "AlGaAs" ("Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") with graded) and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and (sens\$5 detect\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/05/17 14:13
27	(AlGaAs GaAlAs "GaAlAs" "Ga Al As" aluminum adj gallium adj arsinide "Al Ga As" "AlGaAs" ("Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As")) and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and (sens\$5 detect\$5) and (barrier with graded)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/05/17 10:20
30	(AlGaAs GaAlAs "GaAlAs" "Ga Al As" aluminum adj gallium adj arsenide "Al Ga As" "AlGaAs" ("Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As")) and ("Ga As" gallium adj arsenide "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and (sens\$5 detect\$5) and (barrier with graded)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/05/17 10:22
1826	(AlGaAs GaAlAs "GaAlAs" "Ga Al As" aluminum adj gallium adj arsenide "Al Ga As" "AlGaAs" ("Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") with graded) and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/05/17 10:24

	2326	<p>(AlGaAs GaAlAs "GaAlAs" "Ga Al As" aluminum adj gallium adj arsenide "Al Ga As" "AlGaAs" ("Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") with graded) and ("Ga As" gallium adj arsenide "GaAs" GaAs) and (InGaAs GaInAs "GaInAs" "Ga In As" indium adj gallium adj arsenide gallium adj indium adj arsenide "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As")</p>	<p>USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB</p>	2001/05/17 10:27
	601	<p>((((AlGaAs GaAlAs "GaAlAs" "Ga Al As" aluminum adj gallium adj arsinide "Al Ga As" "AlGaAs" ("Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") with graded) and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and (sens\$5 detect\$5)) ((AlGaAs GaAlAs "GaAlAs" "Ga Al As" aluminum adj gallium adj arsinide "Al Ga As" "AlGaAs" ("Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As")) and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and (sens\$5 detect\$5) and (barrier with graded)) ((AlGaAs GaAlAs "GaAlAs" "Ga Al As" aluminum adj gallium adj arsenide "Al Ga As" "AlGaAs" ("Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As")) and ("Ga As" gallium adj arsenide "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and (sens\$5 detect\$5) and (barrier with graded)) ((AlGaAs GaAlAs "GaAlAs" "Ga Al As" aluminum adj gallium adj arsenide "Al Ga As" "AlGaAs" ("Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") with graded) and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As")) ((AlGaAs GaAlAs "GaAlAs" "Ga Al As" aluminum adj gallium adj arsenide "Al Ga As" "AlGaAs" ("Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") with graded) and ("Ga As" gallium adj arsenide "GaAs" GaAs) and (InGaAs GaInAs "GaInAs" "Ga In As" indium adj gallium adj arsenide gallium adj indium adj arsenide "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As"))) and (257/\$ 438/\$) and (sens\$5 detect\$5 photo adj (sens\$5 detect\$5) photosens\$5 photodetect\$5)</p>	<p>USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB</p>	2001/05/17 10:36

..	513	<p>(((AlGaAs GaAlAs "GaAlAs" "Ga Al As" aluminum adj gallium adj arsinide "Al Ga As" "AlGaAs" ("Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") with graded) and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and (sens\$5 detect\$5)) ((AlGaAs GaAlAs "GaAlAs" "Ga Al As" aluminum adj gallium adj arsinide "Al Ga As" "AlGaAs" ("Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As")) and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and (sens\$5 detect\$5) and (barrier with graded)) ((AlGaAs GaAlAs "GaAlAs" "Ga Al As" aluminum adj gallium adj arsenide "Al Ga As" "AlGaAs" ("Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As")) and ("Ga As" gallium adj arsenide "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and (sens\$5 detect\$5) and (barrier with graded)) ((AlGaAs GaAlAs "GaAlAs" "Ga Al As" aluminum adj gallium adj arsenide "Al Ga As" "AlGaAs" ("Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") with graded) and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As")) ((AlGaAs GaAlAs "GaAlAs" "Ga Al As" aluminum adj gallium adj arsenide "Al Ga As" "AlGaAs" ("Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") with graded) and ("Ga As" gallium adj arsenide "GaAs" GaAs) and (InGaAs GaInAs "GaInAs" "Ga In As" indium adj gallium adj arsenide gallium adj indium adj arsenide "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As"))) and (257/\$ 438/\$) and (sens\$5 detect\$5 photo adj (sens\$5 detect\$5) photosens\$5 photodetect\$5)) and well</p>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/05/17 10:36
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--	269	<p>(((AlGaAs GaAlAs "GaAlAs" "Ga Al As" aluminum adj gallium adj arsinide "Al Ga As" "AlGaAs" ("Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") with graded) and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and (sens\$5 detect\$5)) ((AlGaAs GaAlAs "GaAlAs" "Ga Al As" aluminum adj gallium adj arsinide "Al Ga As" "AlGaAs" ("Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and (sens\$5 detect\$5) and (barrier with graded)) ((AlGaAs GaAlAs "GaAlAs" "Ga Al As" aluminum adj gallium adj arsenide "Al Ga As" "AlGaAs" ("Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As")) and ("Ga As" gallium adj arsenide "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and (sens\$5 detect\$5) and (barrier with graded)) ((AlGaAs GaAlAs "GaAlAs" "Ga Al As" aluminum adj gallium adj arsenide "Al Ga As" "AlGaAs" ("Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") with graded) and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As")) ((AlGaAs GaAlAs "GaAlAs" "Ga Al As" aluminum adj gallium adj arsenide "Al Ga As" "AlGaAs" ("Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") with graded) and ("Ga As" gallium adj arsenide "GaAs" GaAs) and (InGaAs GaInAs "GaInAs" "Ga In As" indium adj gallium adj arsenide gallium adj indium adj arsenide "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As"))) and (257/\$ 438/\$) and (sens\$5 detect\$5 photo adj (sens\$5 detect\$5) photosens\$5 photodetect\$5)) and well) and quantum adj well</p>	<p>USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB</p>	2001/05/17 11:25
-	12	<p>((("5869844") or ("5086327") or ("5187715") or ("5228777") or ("5326984") or ("5506418") or ("5677544") or ("5726500") or ("5712499") or ("5719670") or ("5684817") or ("5739949"))).PN.</p>	USPAT	2001/05/17 10:45
-	534	<p>(257/17,21,185).CCLS.</p>	USPAT	2002/02/13 16:00

-	53	((((AlGaAs GaAlAs "GaAlAs" "Ga Al As" aluminum adj gallium adj arsinide "Al Ga As" "AlGaAs" ("Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") with graded) and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and (sens\$5 detect\$5)) ((AlGaAs GaAlAs "GaAlAs" "Ga Al As" aluminum adj gallium adj arsinide "Al Ga As" "AlGaAs" ("Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") with graded) and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and (sens\$5 detect\$5) and (barrier with graded)) ((AlGaAs GaAlAs "GaAlAs" "Ga Al As" aluminum adj gallium adj arsinide "Al Ga As" "AlGaAs" ("Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") with graded) and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and (sens\$5 detect\$5) and (barrier with graded)) ((AlGaAs GaAlAs "GaAlAs" "Ga Al As" aluminum adj gallium adj arsinide "Al Ga As" "AlGaAs" ("Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") with graded) and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As")) ((AlGaAs GaAlAs "GaAlAs" "Ga Al As" aluminum adj gallium adj arsinide "Al Ga As" "AlGaAs" ("Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") with graded) and ("Ga As" gallium adj arsinide "GaAs" GaAs) and (InGaAs GaInAs "GaInAs" "Ga In As" indium adj gallium adj arsinide gallium adj indium adj arsinide "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As")) and (257/\$ 438/\$) and (sens\$5 detect\$5 photo adj (sens\$5 detect\$5) photosens\$5 photodetect\$5)) and well) and quantum adj well) and (("257/17,21,185").CCLS.)	USPAT	2001/05/17 13:59
-	214	piezoelectric near semiconductor	USPAT	2001/05/17 14:00
-	19	piezoelectric near semiconductor with electric adj field	USPAT	2001/05/17 14:03
-	601	piezoelectric with natural adjelectric adj field	USPAT	2001/05/17 14:04
-	601	piezoelectric with natural adjelectric adj field with semiconductor	USPAT	2001/05/17 14:04
-	0	piezoelectric near semiconductor with natural adj electric adj field	USPAT	2001/05/17 14:05
-	0	piezoelectric with natural adj electric adj field	USPAT	2001/05/17 14:05
-	0	piezoelectric same natural adj electric adj field	USPAT	2001/05/17 14:16
-	6	natural adj electric adj field	USPAT	2001/05/17 14:05
-	428	(AlGaAs GaAlAs "GaAlAs" "Ga Al As" aluminum adj gallium adj arsinide "Al Ga As" "AlGaAs" ("Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As")) and ("Ga As" gallium adj arsinide "GaAs" GaAs) and ("Ga In As" "GaInAs" GaInAs Indium adj gallium adj arsinide InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") with (quantum adj well)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/05/17 14:31
-	3	piezoelectric adj field with quantum adj well	USPAT	2001/05/17 14:26
-	2	(AlGaAs GaAlAs "GaAlAs" "Ga Al As" aluminum adj gallium adj arsinide "Al Ga As" "AlGaAs" ("Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As")) and ("Ga As" gallium adj arsinide "GaAs" GaAs) and ("Ga In As" "GaInAs" GaInAs Indium adj gallium adj arsinide InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") with (piezoelectric adj field)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/05/17 14:54
-	2	(gallium adj arsinide GaAs "Ga As" "GaAs") with (piezoelectric adj field)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/05/17 16:36

-	2	((("257/17,21,185").CCLS.) and (electric adj field with doped adj semiconductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/09 14:43
-	52	electric adj field with doped adj semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/05/17 16:38
-	12	electric adj field with doped adj semiconductor adj layer\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/05/17 17:56
-	172	ohmic adj contact\$1 and ((("257/17,21,185").CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/05/17 17:57
-	8	5506418.URPN.	USPAT	2001/05/18 07:54
-	1	5594750.URPN.	USPAT	2001/05/18 07:57
-	3	("5268582" "5481397" "5506418").PN.	USPAT	2001/05/18 07:58
-	10	5416338.URPN.	USPAT	2001/05/18 08:06
-	14	5121181.URPN.	USPAT	2001/05/18 08:30
-	0	RE34649.URPN.	USPAT	2001/05/18 08:34
-	9	("Re32893" "4796067" "4822992" "4894526" "4903101" "5010517" "5036371" "5121181" "5185647").PN.	USPAT	2001/05/18 08:35
-	16	("4203124" "4383269" "4390889" "4471370" "4587544" "4616241" "4631566" "4711857" "4712121" "4722907" "4739385" "4761680" "4814837" "4826295" "4851886" "4903101").PN.	USPAT	2001/05/18 08:35
-	896	((("257/17,21,185").CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/26 14:36
-	9	composition with gradient and (((("257/17,21,185").CCLS.))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/09 14:56
-	47	composition with gradient with transfer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/09 15:23
-	4	composition with gradient with transfer and (438/\$ 257/\$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/09 15:45
-	2	((AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As"))) same composition with gradient	USPAT	2001/10/09 15:44

-	5	composition with grad\$4 with transfer and (438/\$ 257/\$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/09 15:54
-	77	composition with grad\$4 with barrier and (438/\$ 257/\$) not (composition with grad\$4 with transfer and (438/\$ 257/\$))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/10 09:03
-	23	(composition with grad\$4 with barrier and (438/\$ 257/\$) not (composition with grad\$4 with transfer and (438/\$ 257/\$))) and III-V	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/09 16:37
-	54	(composition with grad\$4 with barrier and (438/\$ 257/\$) not (composition with grad\$4 with transfer and (438/\$ 257/\$))) not ((composition with grad\$4 with barrier and (438/\$ 257/\$) not (composition with grad\$4 with transfer and (438/\$ 257/\$))) and III-V)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/09 16:38
-	22	DEVEAUD-PLEDRAN-B DEVEAUD-PLEDRAN-BENOIT DEVEAUD-PLEDRAN-ET-AL DEVEAUD-PLEDRAN	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/10 09:14
-	36	VINTER-BORGE VINTER-ET-AL	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/10 09:14
-	22	VINTER-BORGE	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/10 11:48
-	1	("5432362").PN.	USPAT	2001/10/10 09:25
-	1	("5311211").PN.	USPAT	2001/10/10 09:25
-	1	("5311221").PN.	USPAT	2001/10/10 09:27
-	2250	decreas\$3 with (emitt\$3 near8 collect\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/10 09:30
-	41	decreas\$3 with (emitt\$3 near8 collect\$3) with (band adj gap energy)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/10 10:01
-	80	ROSENCHER-EMMANUEL ROSENCHER-ET-AL ROSENCHER	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/10 10:07
-	10	(VINTER-BORGE VINTER-ET-AL) and (ROSENCHER-EMMANUEL ROSENCHER-ET-AL ROSENCHER)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/10 10:07

-	2	ohmic adj contact\$1 with electron adj storage adj layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/10 13:53
-	1	("5429957").PN.	USPAT	2001/10/10 13:53
-	921	(257/17,21,185).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/13 16:46
-	594	well\$1 and ((257/17,21,185).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/13 16:46
-	422	barrier and (well\$1 and ((257/17,21,185).CCLS.))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/13 16:48
-	422	(barrier and (well\$1 and ((257/17,21,185).CCLS.))) and pd@>=20011009	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/13 16:48
-	14	(barrier and (well\$1 and ((257/17,21,185).CCLS.))) and @pd>=20011009	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/13 16:49
-	0	BERGER-VINCANT BERGER-VINCENT	US-PGPUB	2002/09/26 13:38
-	0	BERGER-VINCANT BERGER-VINCENT	US-PGPUB	2002/09/26 13:39
-	19	BERGER-VINCANT BERGER-VINCENT	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/26 13:53
-	0	967662.URPN.	USPAT	2002/09/26 13:44
-	4	BERGER-VINCANT BERGER-VINCENT BERGER-V	USPAT; US-PGPUB	2002/09/26 13:54
-	0	BERGER-VINCANT BERGER-VINCENT BERGER-V	US-PGPUB	2002/09/26 13:54
-	973	((("257/17,21,185").CCLS.))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/26 14:36
-	44	((("257/17,21,185").CCLS.)) and @pd>=20020213	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/14 11:34
-	13	((("257/17,21,185").CCLS.)) and @pd>=20020926 and barrier and well	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/14 11:36
-	1	transfer near barrier with (angstrom ang nm nanometer nano micron micrometer micro thick thickness) same quantum near well with (angstrom ang nm nanometer nano micron micrometer micro thick thickness)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/06 09:19

-	1648	barrier with (angstrom ang nm nanometer nano micron micrometer micro thick thickness) same quantum near well with (angstrom ang nm nanometer nano micron micrometer micro thick thickness) not (transfer near barrier with (angstrom ang nm nanometer nano micron micrometer micro thick thickness) same quantum near well with (angstrom ang nm nanometer nano micron micrometer micro thick thickness))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/06 09:29
-	2759	(257/11,189,200,201,615,745,e31.019,e31.026,e31.059,e33.049,e33.023,e33.037,3e7.089,e27.012).CCLS	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/06 09:27
-	64	(barrier with (angstrom ang nm nanometer nano micron micrometer micro thick thickness) same quantum near well with (angstrom ang nm nanometer nano micron micrometer micro thick thickness) not (transfer near barrier with (angstrom ang nm nanometer nano micron micrometer micro thick thickness) same quantum near well with (angstrom ang nm nanometer nano micron micrometer micro thick thickness))) and ((257/11,189,200,201,615,745,e31.019,e31.026,e31.059,e33.049,e33.023,e33.037,3e7.089,e27.012).CCL	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/06 14:33

L Number	Hits	Search Text	DB	Time stamp
1	2	("5955772").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/06 14:34
3	0	(transfer near barrier with (angstrom ang nm nanometer nano micron micrometer micro thick thickness)) same quantum near well with (angstrom ang nm nanometer nano micron micrometer micro thick thickness) and ((257/17,21,85).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/06 14:47